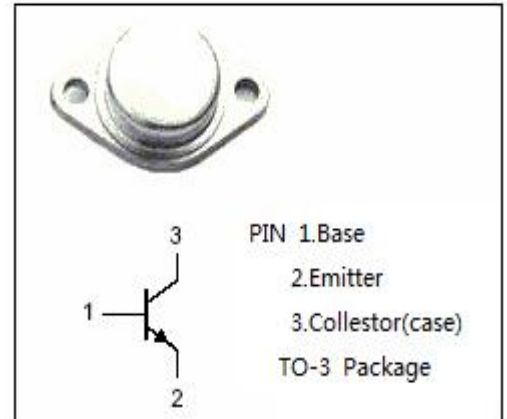


**isc Silicon NPN Power Transistor**
**BDY57**
**DESCRIPTION**

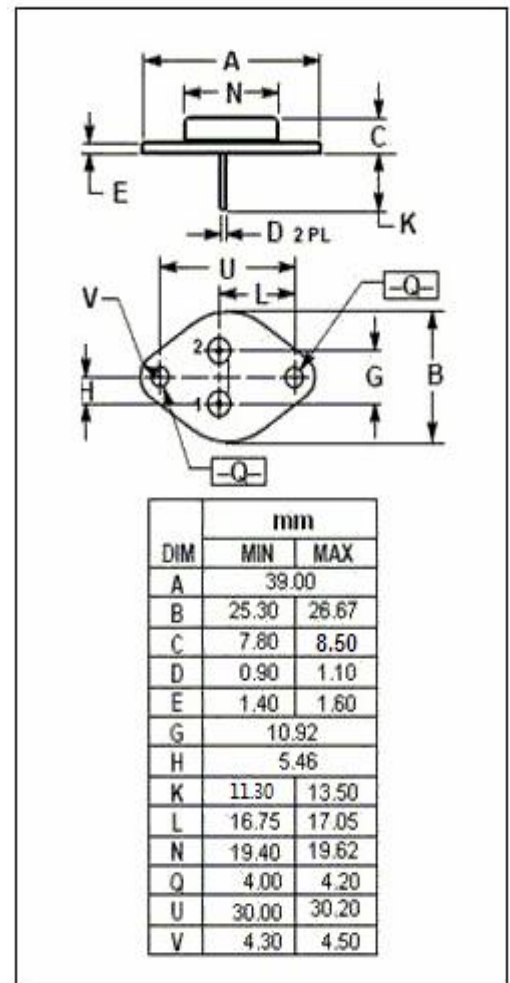
- Collector-Emitter Sustaining Voltage-  
:  $V_{CEO(SUS)} = 80V(\text{Min})$
- High Power Dissipation
- Low Collector Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- LF signal power amplification.
- High current fast switching


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector- Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	10	V
$I_C$	Collector Current-Continuous	25	A
$I_B$	Base Current-Continuous	6	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	175	W
$T_J$	Junction Temperature	200	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-65~200	$^\circ\text{C}$


**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.0	$^\circ\text{C/W}$

## isc Silicon NPN Power Transistor

## BDY57

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE0(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 30mA ; I <sub>B</sub> = 0	80			V
V <sub>(BR)CBO</sub>	Collector- Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	120			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA ; I <sub>C</sub> = 0	10			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 1A			1.4	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			0.5	mA
I <sub>CER</sub>	Collector Cutoff Current	V <sub>CE</sub> = 80V; R <sub>BE</sub> = 10 Ω V <sub>CE</sub> = 80V; R <sub>BE</sub> = 10 Ω ; T <sub>C</sub> =100°C			0.5 10	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 10V; I <sub>C</sub> = 0			0.5	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 10A ; V <sub>CE</sub> = 4V	20		80	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 20A ; V <sub>CE</sub> = 4V		15		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 1A ; V <sub>CE</sub> = 15V; f= 10MHz	10			MHz
Switching Times						
t <sub>on</sub>	Turn-On Time	I <sub>C</sub> = 15A , I <sub>B</sub> = 1.5A,			1.0	μ s
t <sub>off</sub>	Turn-Off Time	I <sub>C</sub> = 15A , I <sub>B1</sub> = -I <sub>B2</sub> = 1.5A,			2.0	μ s

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